

UTMC APPLICATION NOTE

UT22VP10 RADPAL Characterization Summary

Table 1: AC Electrical Characterization Summary

Parameter	Sample Size	Worst Case	Conditions
t _{PD}	56	17.3ns	-55°C,+125°C
t _{EA}	3	21.1ns	-55°C,+125°C
t _{ER}	3	19.26ns	-55°C,+125°C
t _H	56	0.40ns	-55°C,+125°C
t _{SU}	56	7.6ns	-55°C,+125°C
t _P	56	19.5ns	-55°C,+125°C
t _{CO}	56	11.9ns	-55°C,+125°C
t _{CO2}	56	21.1ns	-55°C,+125°C
t _{WL}	4	<10.0ns	-55°C,+125°C
t _{WH}	4	<10.0ns	-55°C,+125°C
t _{CF}	1	8.0ns	-55°C,+125°C
t _{AW}	56	8.5ns	-55°C,+125°C
t _{AR}	56	2.3ns	-55°C,+125°C
t _{AP}	56	15.4ns	-55°C,+125°C
t _{SPR}	56	1.3ns	-55°C,+125°C
f _{MAX1}	56	51.3MHz	-55°C,+125°C
f _{MAX2}	56	>50.0 MHz	-55°C,+125°C
f _{MAX3}	56	50.2 MHz	-55°C,+125°C

Table 2: DC Electrical Characterization Summary

Parameter	Sample Size	Worst Case	Conditions
V _{IL}	4	2.16V	CMOS -55°C,+125°C
V _{IH}	4	2.36V	CMOS -55°C,+125°C
V _{IL}	4	1.48V	TTL -55°C,+125°C
V _{IH}	4	2.06V	TTL -55°C,+125°C
V _{OL}	5	0.007V	CMOS -55°C,+125°C
V _{OH}	5	4.465V	CMOS -55°C,+125°C
V _{OL}	5	0.252V	TTL -55°C,+125°C
V _{OH}	5	4.373V	TTL -55°C,+125°C
I _{IN}	10	0.032μA	-55°C,+125°C
I _{OS}	2	123.55mA	-55°C,+125°C
I _{OZ}	10	1.886μA	-55°C,+125°C
I _{CC}	4	98.4mA	-55°C,+125°C
ESD	3	<500V	25°C